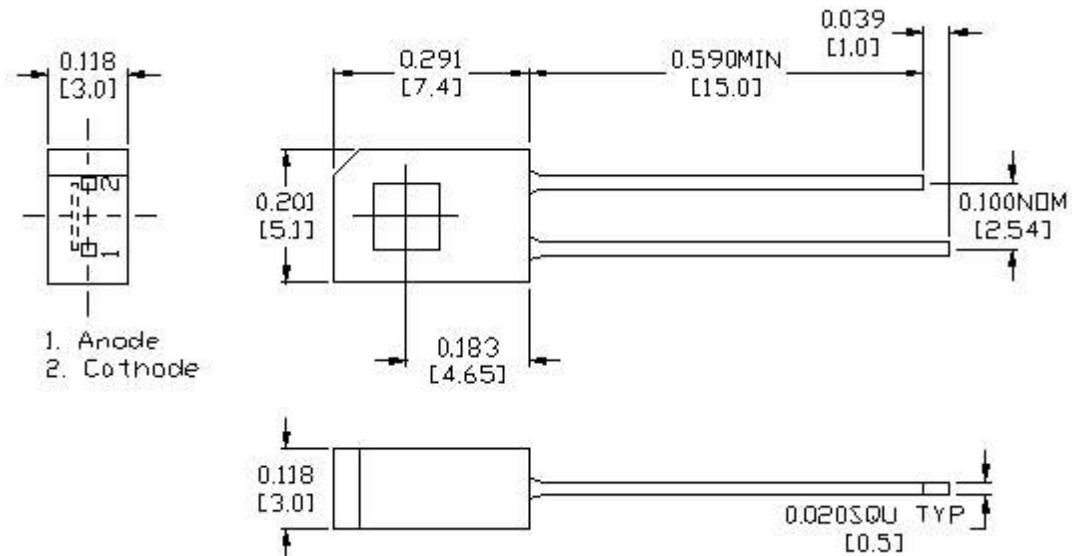


DESCRIPTION

This is a Silicon Photo Diode optimized for applications requiring a wide viewing angle and a side-looking package.

FEATURES

- High Responsivity
- Wide Viewing Angle
- Side-looking Plastic Package



ABSOLUTE MAXIMUM RATINGS

- Storage temperature..... -20°C to +85°C
- Case operating temperature..... 0°C to +70°C
- Lead solder temperature..... 260°C, 10 seconds
- Reverse Breakdown Voltage..... 35 Volts

OUTLINE DIMENSIONS

Tolerances are +/-0.005 inches, except as noted
The case is electrically isolated from the pins.

PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP	MAX	UNIT
Capacitance	Vr = 10 V, f = 1 MHz	C		10		pF
Open Circuit Voltage	H = 5.0 mW/cm ²	VOC		350		mV
Short Circuit Current	H = 5.0 mW/cm ²	ISC	50	75		µA
Dark Current	Vr = 10 Volts, H = 0 mW	Id		5	30	nA
Response Time	10%-90%, Vr = 10 Volts Rl = 1K Ω	tr tf		50 50		nsec nsec
Peak Wavelength		λ		940		nm
Electrical Bandwidth	Vr = 10 Volts	BWE		10		MHz
Reverse Light Current	H=5.0 mW/cm ² , Vr=5 V	IL	60	120		µA
Viewing Angle		2 θ1/2		140		Deg

ELECTRO-OPTICAL CHARACTERISTICS (Case T = 25°C)

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